

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)

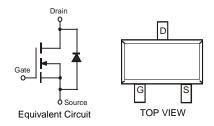
Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

SOT-323







Maximum Ratings @T_A = 25°C unless otherwise specified

Characteris	etic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V	
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ		V_{DGR}	60	V	
Gain-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V	
Drain Current (Note 1)	Continuous Continuous @ 100°C Pulsed	I _D	115 73 800	mA	

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	D	200	mW
Derating above T _A = 25°C	P_{D}	1.60	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C /W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

 2. No purposefully added lead.

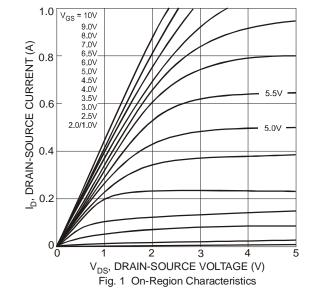
 $T_j = 25^{\circ}C$

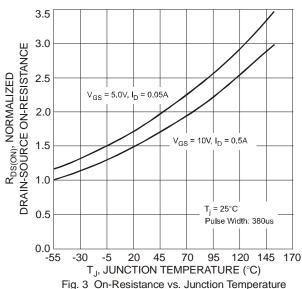


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 3)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current @ T _C	= 25°C	Inno			1.0	μА	$V_{DS} = 60V, V_{GS} = 0V$
@ T _C = 125°C		I _{DSS}			500	μΛ	VDS = 00 V, VGS = 0 V
Gate-Body Leakage		IGSS	_		±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 3)		•			•		•
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance @ TJ	= 25°C	D		1.8	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
® T _j = 125°C		R _{DS(ON)}	_	2.6	13.5	2.2	$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0		Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g _{FS}	80	_		mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS				a.			
Input Capacitance		C _{iss}	_	22	50	pF	V 25V V 0V
Output Capacitance Reverse Transfer Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
		C _{rss}	_	2.0	5.0	pF	1 = 1.00012
SWITCHING CHARACTERISTICS			,				
Turn-On Delay Time		t _{D(ON)}	_	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}	_	11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

Notes: 3. Short duration pulse test used to minimize self-heating effect.





BON 'NORWALIZED ON 'N

0.4

I_D, DRAIN CURRENT (A)

Fig. 2 On-Resistance vs. Drain Current

V_{GS} = 5.0V

V_{GS} = 10V

0.6

8.0

1.0

DRAIN-SOURCE ON-RESISTANCE

0

6

0

0.2

R_{DS(ON)}, NORMALIZED

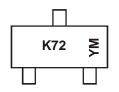


Ordering Information (Notes 4)

Part Number	Case	Packaging			
2N7002W-7-F	SOT-323	3000/Tape & Reel			

Notes: 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K72 = Product Type Marking Code

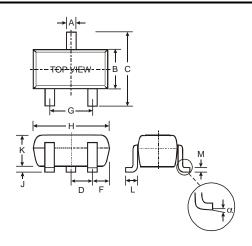
YM = Date Code Marking

Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

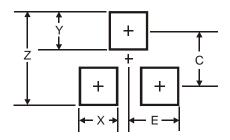
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Χ	Υ	Z
Month	Jan	Fel	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Ос	t	Nov	Dec
Code	1	2		3	4	5	6	;	7	8	9	0		N	D

Package Outline Dimensions



SOT-323						
Dim	Min	Max				
Α	0.25	0.40				
В	1.15	1.35				
С	2.00	2.20				
D	0.65 N	ominal				
F	0.30	0.40				
G	1.20 1.40					
Н	1.80	2.20				
J	0.0 0.10					
K	0.90 1.00					
L	0.25	0.40				
M	0.10	0.18				
α	0°	8°				
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Υ	0.9
С	1.9
Е	1.0

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